PD-97292A

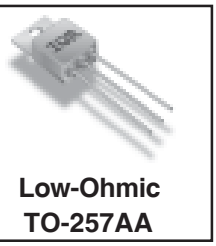
International
IOR Rectifier

RADIATION HARDENED LOGIC LEVEL POWER MOSFET THRU-HOLE (Low-Ohmic TO-257AA)

2N7625T3
IRHLYS797034CM
60V, P-CHANNEL
R7™ TECHNOLOGY

Product Summary

Part Number	Radiation Level	$R_{DS(on)}$	I_D
IRHLYS797034CM	100K Rads (Si)	0.074Ω	-20A*
IRHLYS793034CM	300K Rads (Si)	0.074Ω	-20A*



Low-Ohmic TO-257AA

International Rectifier's R7™ Logic Level Power MOSFETs provide simple solution to interfacing CMOS and TTL control circuits to power devices in space and other radiation environments. The threshold voltage remains within acceptable operating limits over the full operating temperature and post radiation. This is achieved while maintaining single event gate rupture and single event burnout immunity.

These devices are used in applications such as current boost low signal source in PWM, voltage comparator and operational amplifiers.

Features:

- 5V CMOS and TTL Compatible
- Fast Switching
- Single Event Effect (SEE) Hardened
- Low Total Gate Charge
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Light Weight
- Complimentary N-Channel Available - IRHLYS77034CM

Absolute Maximum Ratings

Pre-Irradiation

	Parameter		Units
I_D@V_{GS} = -4.5V, T_C = 25°C	Continuous Drain Current	-20*	A
I_D@V_{GS} = -4.5V, T_C = 100°C	Continuous Drain Current	-16.6	
I_{DM}	Pulsed Drain Current ①	-80	
P_D @ T_C = 25°C	Max. Power Dissipation	75	W
	Linear Derating Factor	0.6	W/°C
V_{GS}	Gate-to-Source Voltage	±10	V
E_{AS}	Single Pulse Avalanche Energy ②	181	mJ
I_{AR}	Avalanche Current ①	-20	A
E_{AR}	Repetitive Avalanche Energy ①	7.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	10.9	V/ns
T_J	Operating Junction	-55 to 150	°C
T_{STG}	Storage Temperature Range		
	Lead Temperature	300 (0.063in/1.6mm from case for 10s)	
	Weight	4.3 (Typical)	g

* Current is limited by package

For footnotes refer to the last page

Electrical Characteristics @ Tj = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	-60	—	—	V	V_{GS} = 0V, I_D = -250μA
$\Delta BV_{DSS}/\Delta T_J$	Temperature Coefficient of Breakdown Voltage	—	-0.06	—	V/°C	Reference to 25°C, I_D = -1.0mA
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	—	—	0.074	Ω	V_{GS} = -4.5V, I_D = -16.6A④
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	—	-2.0	V	V_{DS} = V_{GS}, I_D = -250μA
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	3.8	—	mV/°C	
g_{fs}	Forward Transconductance	17	—	—	S	V_{DS} = -10V, I_{DS} = -16.6A ④
I_{DSS}	Zero Gate Voltage Drain Current	—	—	-1.0	μA	V_{DS}= -48V ,V_{GS} =0V
		—	—	-10		V_{DS} = -48V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Leakage Forward	—	—	-100	nA	V_{GS} = -10V
I_{GSS}	Gate-to-Source Leakage Reverse	—	—	100		V_{GS} = 10V
Q_g	Total Gate Charge	—	—	36	nC	V_{GS} = -4.5V, I_D = -20A
Q_{gs}	Gate-to-Source Charge	—	—	14		V_{DS} = -30V
Q_{gd}	Gate-to-Drain ('Miller') Charge	—	—	18		
$t_{d(on)}$	Turn-On Delay Time	—	—	32	ns	V_{DD} = -30V, I_D = -20A, V_{GS} = -5.0V, R_G = 7.5Ω
t_r	Rise Time	—	—	265		
$t_{d(off)}$	Turn-Off Delay Time	—	—	100		
t_f	Fall Time	—	—	85		
$L_S + L_D$	Total Inductance	—	6.8	—	nH	Measured from Drain lead (6mm / 0.025 in from package) to Source lead (6mm/ 0.025 in from package)
Ciss	Input Capacitance	—	2249	—	pF	V_{GS} = 0V, V_{DS} = -25V
C_{oss}	Output Capacitance	—	580	—		f = 1.0MHz
C_{rss}	Reverse Transfer Capacitance	—	86	—		
R_g	Gate Resistance	—	—	20	Ω	f = 1.0MHz, open drain

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-20*	A	
I_{SM}	Pulse Source Current (Body Diode) ①	—	—	-80		
V_{SD}	Diode Forward Voltage	—	—	-5.0	V	T_j = 25°C, I_S = -20A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	—	—	100	ns	T_j = 25°C, I_F = -20A, di/dt ≤ -100A/μs
Q_{RR}	Reverse Recovery Charge	—	—	128	nC	V_{DD} ≤ -25V ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L_S + L_D.				

* Current is limited by package

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R_{thJC}	Junction-to-Case	—	—	1.67	°C/W	
R_{thJA}	Junction-to-Ambient	—	—	80		Typical Socket Mount

Note: Corresponding Spice and Saber models are available on International Rectifier Web site.

For footnotes refer to the last page

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

	Parameter	Up to 300K Rads (Si)[1]		Units	Test Conditions
		Min	Max		
BV_{DSS}	Drain-to-Source Breakdown Voltage	-60	—	V	V_{GS} = 0V, I_D = -250µA
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	-2.0		V_{GS} = V_{DS}, I_D = -250µA
I_{GSS}	Gate-to-Source Leakage Forward	—	-100	nA	V_{GS} = -10V
I_{GSS}	Gate-to-Source Leakage Reverse	—	100		V_{GS} = 10V
I_{DSS}	Zero Gate Voltage Drain Current	—	-1.0	µA	V_{DS}= -48V, V_{GS}= 0V
$R_{DS(on)}$	Static Drain-to-Source ④ On-State Resistance (TO-3)	—	0.076	Ω	V_{GS} = -4.5V, I_D = -16.6A
$R_{DS(on)}$	Static Drain-to-Source On-state ④ Resistance (Low Ohmic TO-257)	—	0.074	Ω	V_{GS} = -4.5V, I_D = -16.6A
V_{SD}	Diode Forward Voltage④	—	-5.0	V	V_{GS} = 0V, I_D = -20A

1. Part numbers IRHLYS797034, IRHLYS793034

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Typical Single Event Effect Safe Operating Area

LET	Energy	Range	VDS (V)					
(MeV/(mg/cm^2))	(MeV)	(µm)	@VGS= 0V	@VGS= 2V	@VGS= 4V	@VGS= 5V	@VGS= 6V	@VGS= 7V
38 ± 5%	300 ± 7.5%	38 ± 7.5%	-60	-60	-60	-60	-60	-40
62 ± 5%	355 ± 7.5%	33 ± 7.5%	-60	-60	-60	-60	-60	-
85 ± 5%	380 ± 7.5%	29 ± 7.5%	-60	-60	-60	-60	-	-

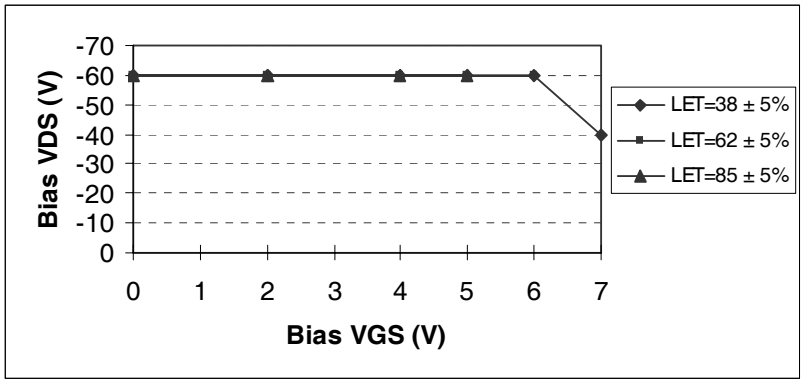


Fig a. Typical Single Event Effect, Safe Operating Area

For footnotes refer to the last page

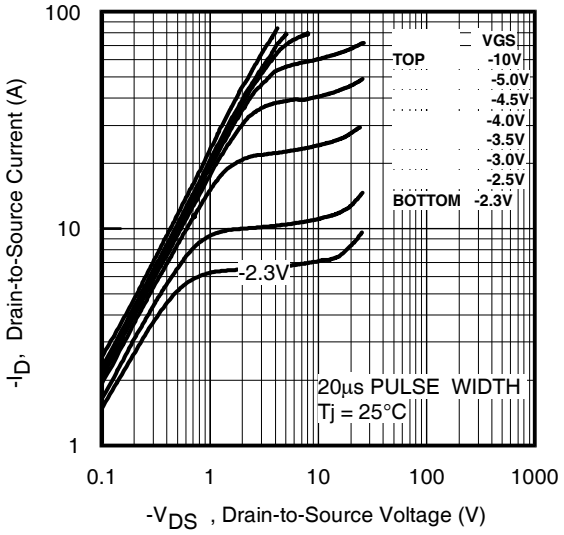


Fig 1. Typical Output Characteristics

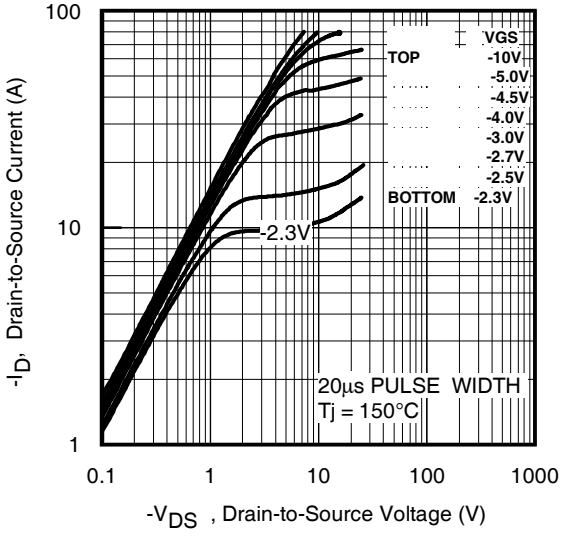


Fig 2. Typical Output Characteristics

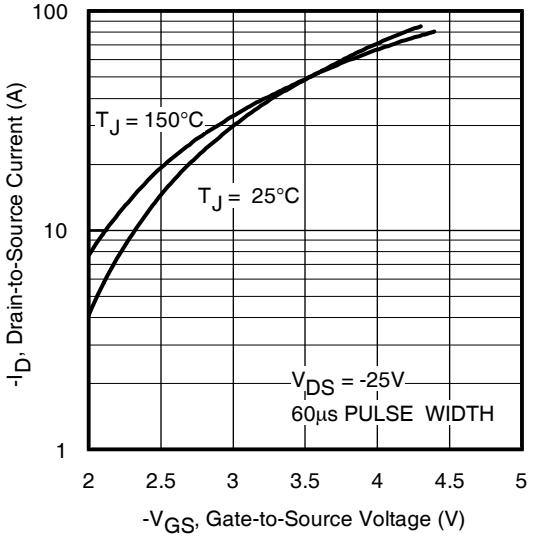


Fig 3. Typical Transfer Characteristics

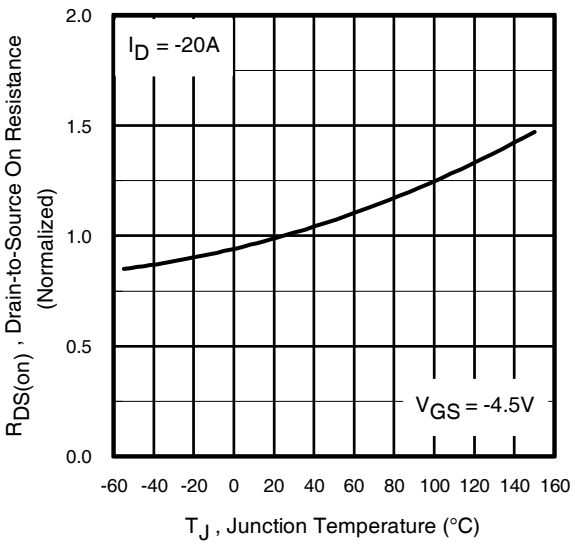


Fig 4. Normalized On-Resistance Vs. Temperature

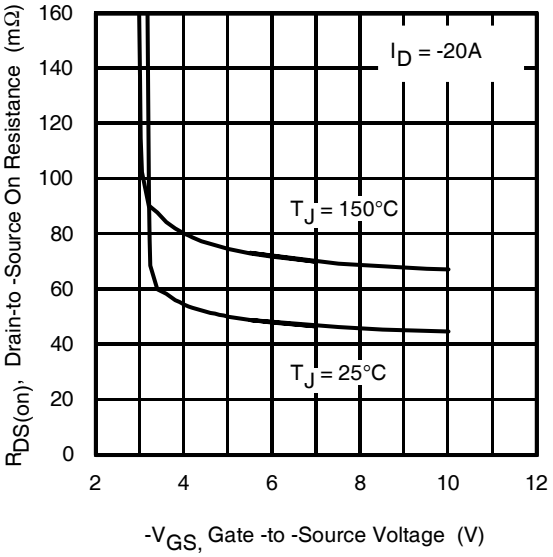


Fig 5. Typical On-Resistance Vs Gate Voltage

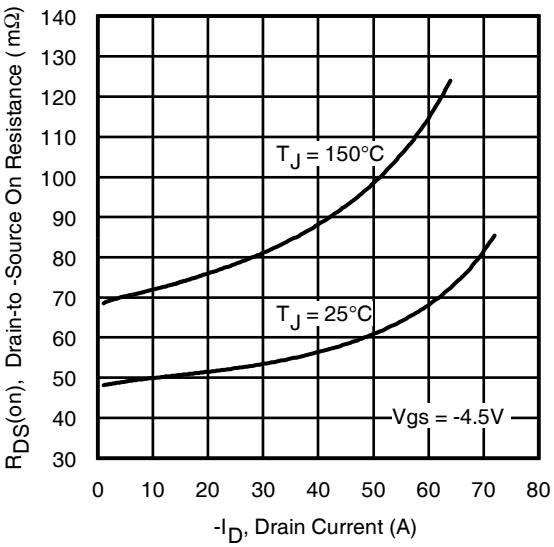


Fig 6. Typical On-Resistance Vs Drain Current

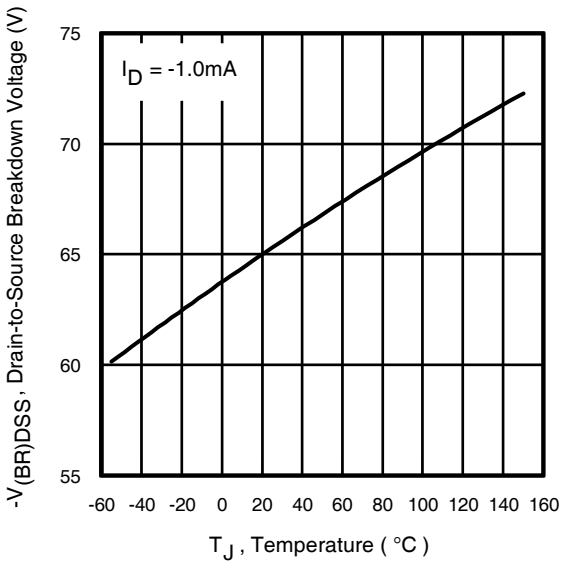


Fig 7. Typical Drain-to-Source Breakdown Voltage Vs Temperature

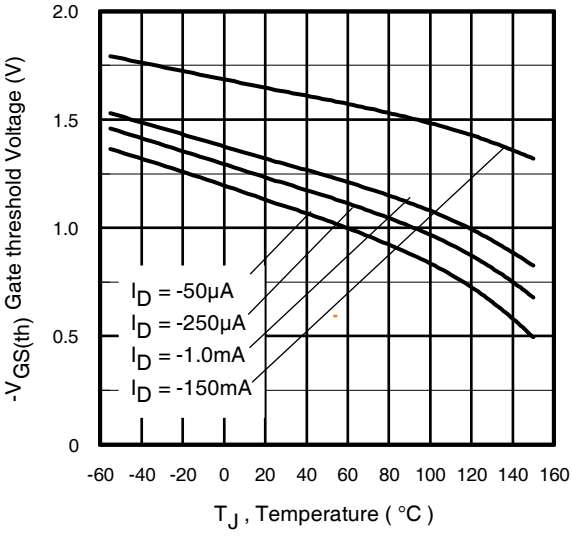


Fig 8. Typical Threshold Voltage Vs Temperature

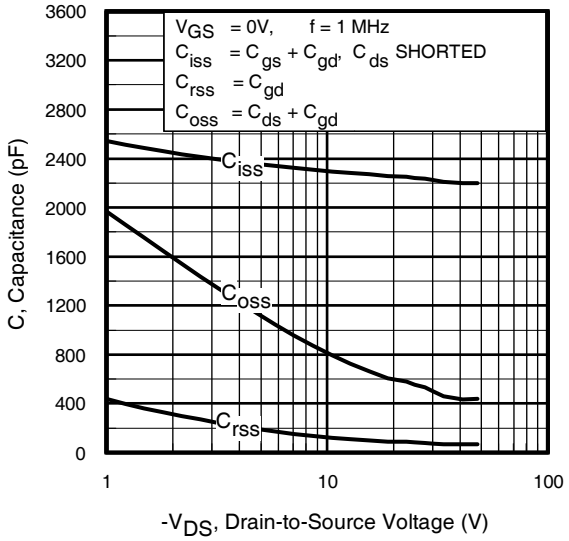


Fig 9. Typical Capacitance Vs. Drain-to-Source Voltage

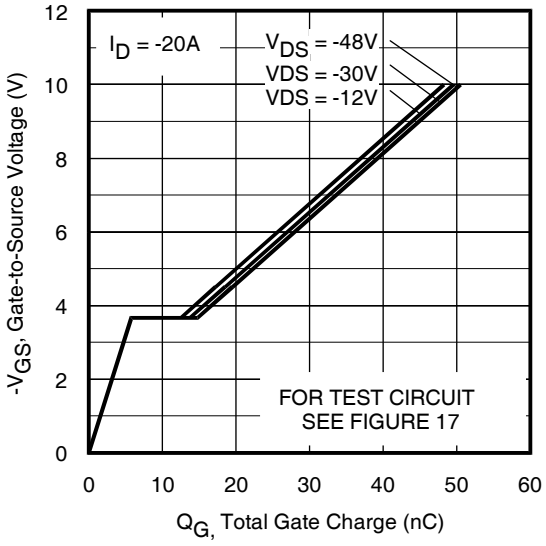


Fig 10. Typical Gate Charge Vs. Gate-to-Source Voltage

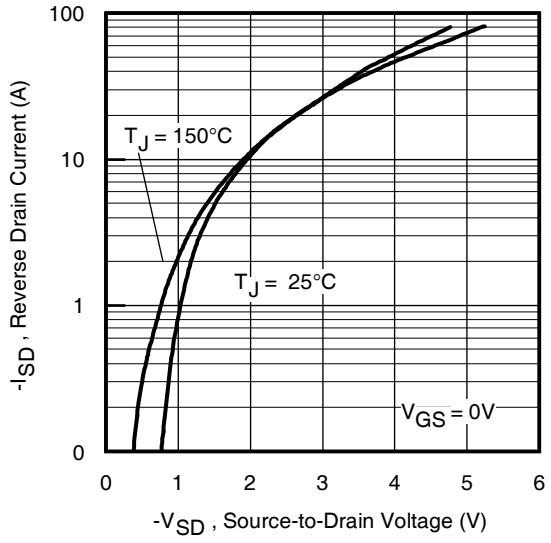


Fig 11. Typical Source-Drain Diode Forward Voltage

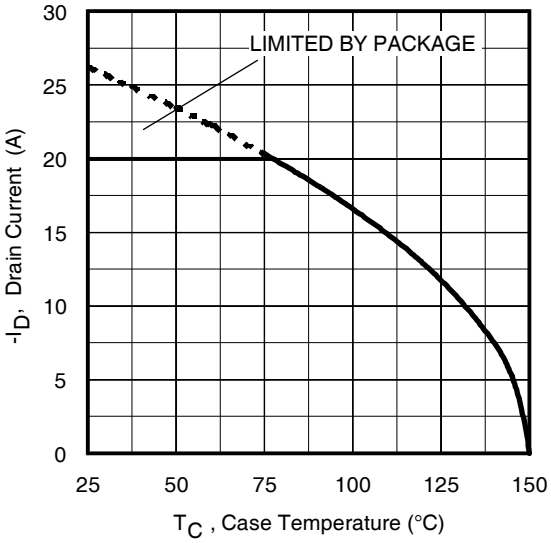


Fig 12. Maximum Drain Current Vs. Case Temperature

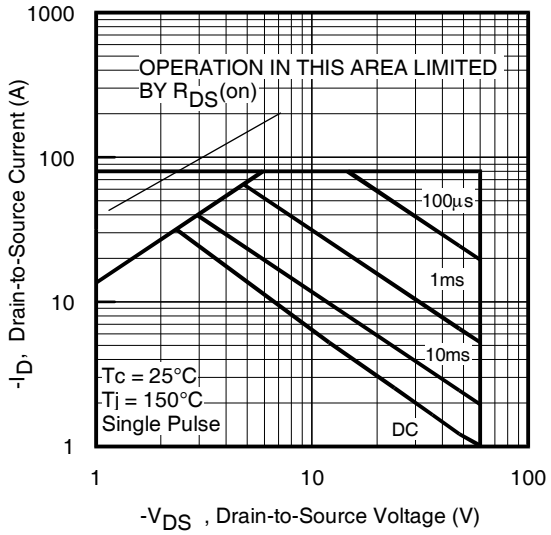


Fig 13. Maximum Safe Operating Area

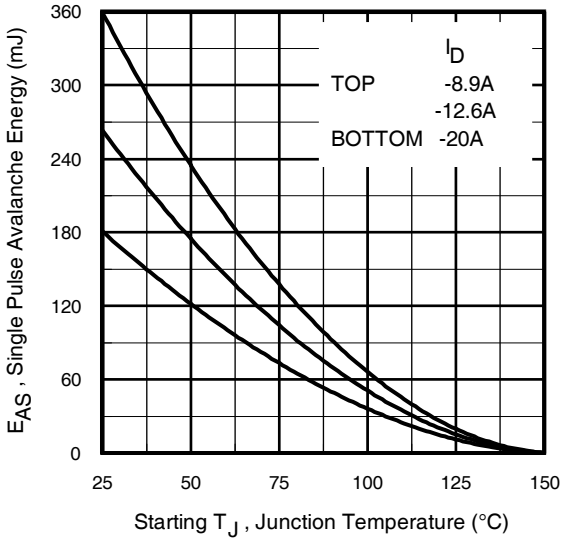


Fig 14. Maximum Avalanche Energy Vs. Drain Current

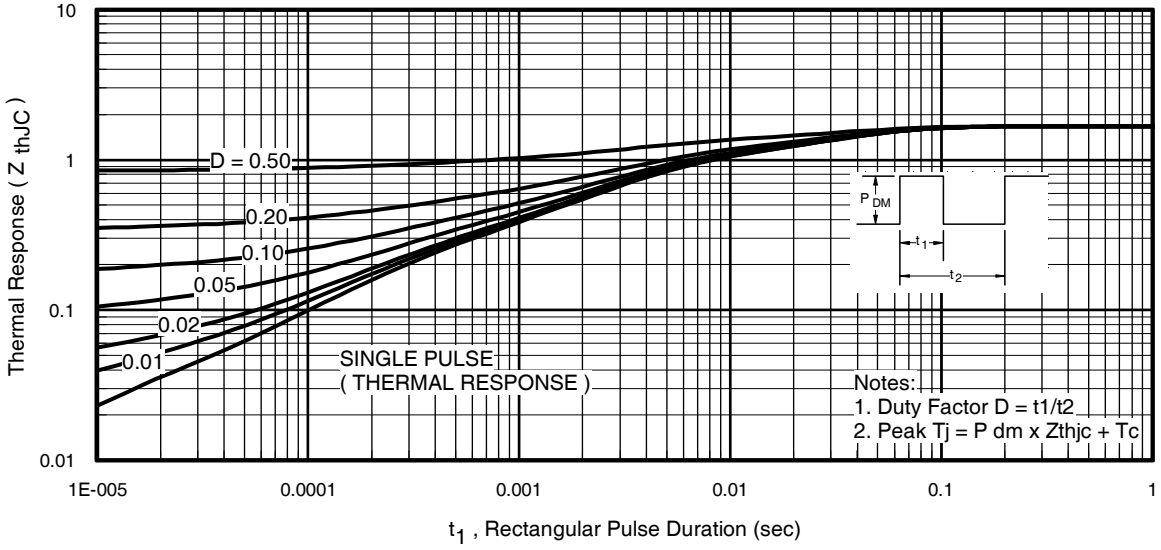


Fig 15. Maximum Effective Transient Thermal Impedance, Junction-to-Case

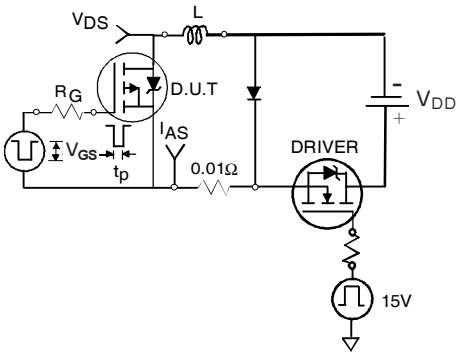


Fig 16a. Unclamped Inductive Test Circuit

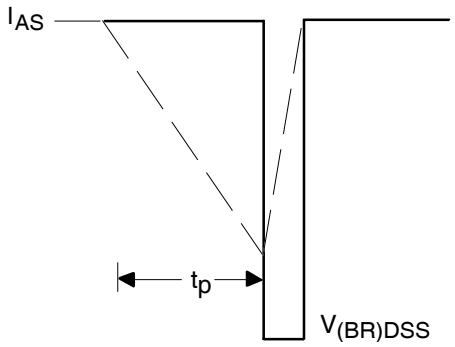


Fig 16b. Unclamped Inductive Waveforms

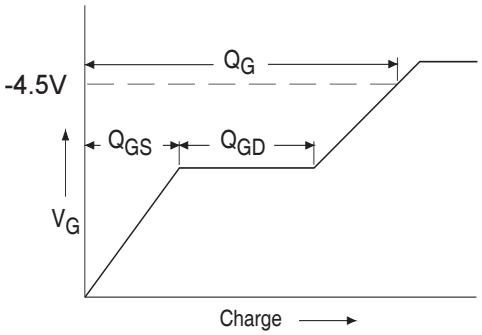


Fig 17a. Basic Gate Charge Waveform

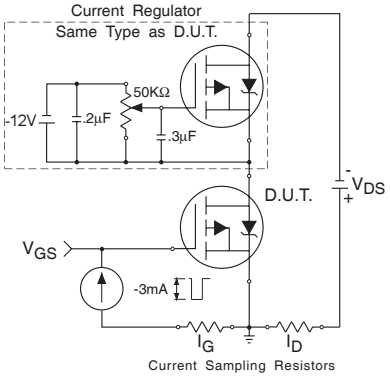


Fig 17b. Gate Charge Test Circuit

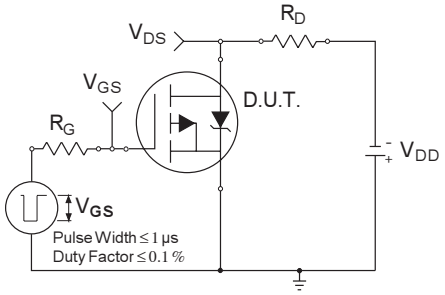


Fig 18a. Switching Time Test Circuit

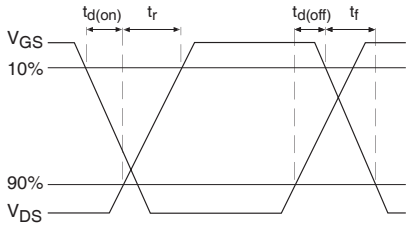


Fig 18b. Switching Time Waveforms

Footnotes:

① Repetitive Rating; Pulse width limited by maximum junction temperature.

② V_{DD} = -25V, starting T_J = 25°C, L = 0.9 mH Peak I_L = -20A, V_{GS} = -10V

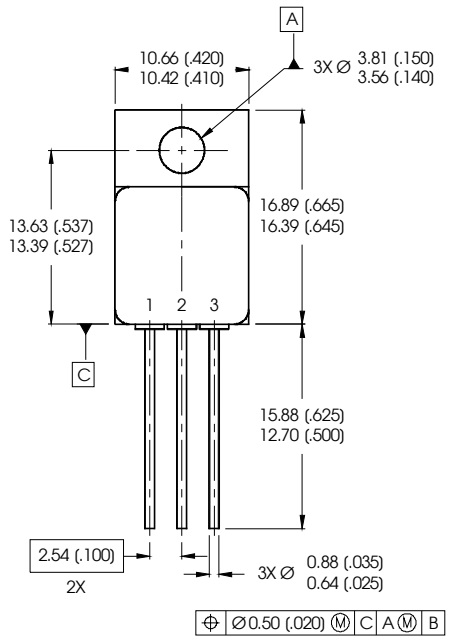
③ I_{SD} ≤ -20A, di/dt ≤ -359A/μs, V_{DD} ≤ -60V, T_J ≤ 150°C

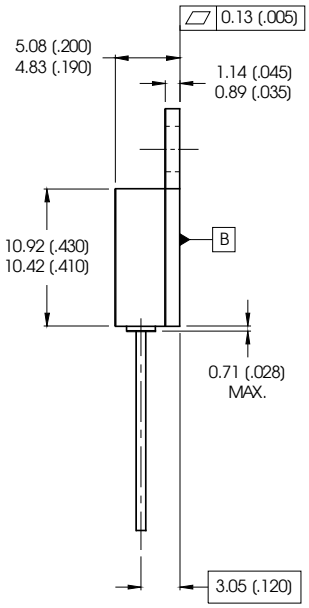
④ Pulse width ≤ 300 μs; Duty Cycle ≤ 2%

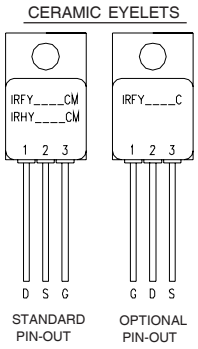
⑤ **Total Dose Irradiation with V_{GS} Bias.** -10 volt V_{GS} applied and V_{DS} = 0 during irradiation per MIL-STD-750, method 1019, condition A.

⑥ **Total Dose Irradiation with V_{DS} Bias.** -48 volt V_{DS} applied and V_{GS} = 0 during irradiation per MIL-STD-750, method 1019, condition A.

Case Outline and Dimensions — Low Ohmic TO-257AA







NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-257AA.

PIN ASSIGNMENTS

1 = DRAIN
2 = SOURCE
3 = GATE

CAUTION

BERYLLIA WARNING PER MIL-PRF-19500

Package containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.

International
IOR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
IR LEOMINSTER : 205 Crawford St., Leominster, Massachusetts 01453, USA Tel: (978) 534-5776
TAC Fax: (310) 252-7903
Visit us at www.irf.com for sales contact information.

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